

# INF3410/4411, Fall 2018

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Excerpt of Sedra/Smith Chapter 15: Inverter Delay

# Content

Digital/Binary and Analog Linear/Small-Signal Abstraction

Logic gates (book 15.1)

Inverter Gate Delay (book 15.4)

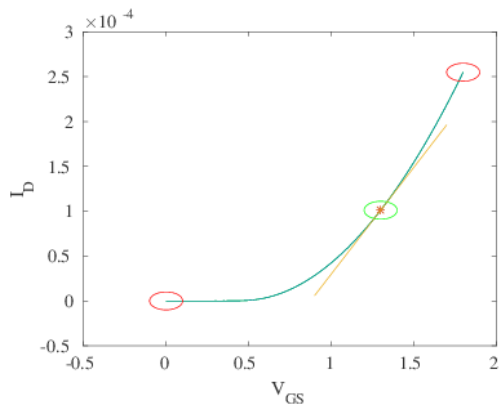
# Content

## Digital/Binary and Analog Linear/Small-Signal Abstraction A digital MOSFET model

Logic gates (book 15.1)

Inverter Gate Delay (book 15.4)

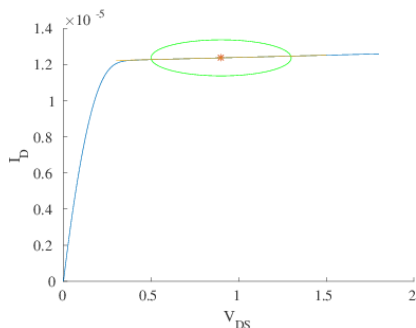
## Digital and Analog Simplifications $i_D$ vs. $v_{GS}$



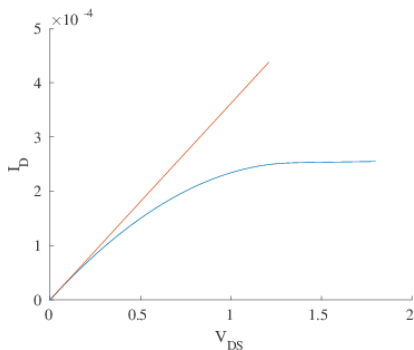
The transistor level digital abstraction only considers the binary input range  $v_{GS} \in \{0, V_{dd}\}$

The transistor level analog abstraction (small signal model) only considers a small input range around a bias point/point of operation and linear output approximation.

## Digital and Analog Simplifications $i_D$ vs. $v_{DS}$

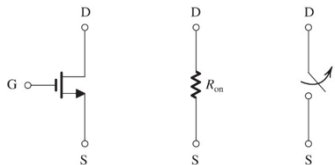


Again the transistor level analog abstraction only considers a small input range around a bias point/point of operation and linear output approximation. In the active region the linear approximation holds for quite a large range for  $v_{DS}$ .



The transistor level digital abstraction also uses a linear approximation here for the two different  $v_{GS}$ : an open circuit and a resistive behaviour  $R_{on} = r_{ds}$ .

# Digital MOSFET Model Variant

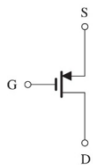


$$V_G = V_{DD} \\ (G = 1)$$

(a)



$$V_G = 0 \\ (G = 0)$$



$$V_G = V_{DD} \\ (G = 1)$$

(b)



$$V_G = 0 \\ (G = 0)$$



Thus in the digital transistor abstraction both pFET and nFET have two conductive states controlled by the input voltage at the gate.

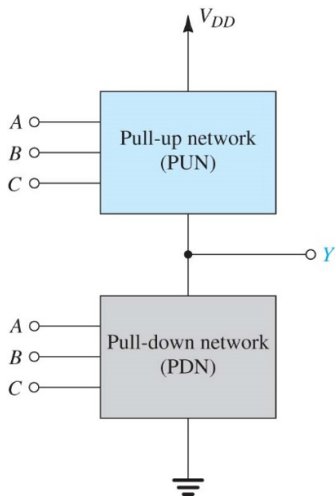
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Digital/Binary and Analog Linear/Small-Signal Abstraction

Logic gates (book 15.1)

Inverter Gate Delay (book 15.4)

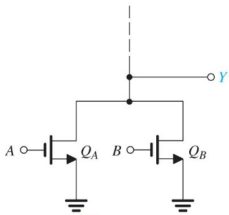
# Pull-Up and Pull-Down



Logic functions can be implemented by complementary pull-up and pull down networks ... or you can just add a resistor tot PUN or PDN... Would that be smart?

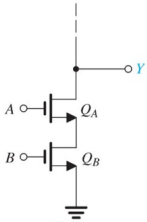


# PDN examples



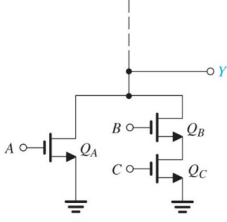
$$\bar{Y} = A + B$$

(a)



$$\bar{Y} = AB$$

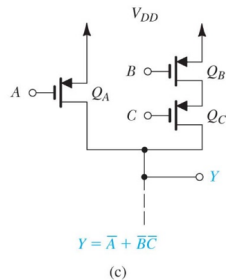
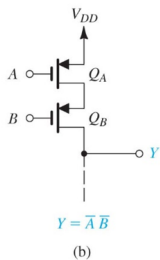
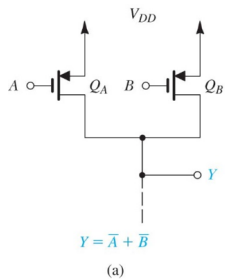
(b)



$$\bar{Y} = A + BC$$

(c)

# PUN examples



## Complementary PUN and PDN

Usually, logic gates are composed of a PUN and PDN that implement each others *inverse* function. Such that always either the PUN or the PDN are active. E.g. the PDN:

$$\bar{Y} = (A + B) * C$$

And the PUN

$$Y = \overline{(A + B) * C} = \dots$$

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Usually, logic gates are composed of a PUN and PDN that implement each others *inverse* function. Such that always either the PUN or the PDN are active. E.g. the PDN:

$$\bar{Y} = (A + B) * C$$

And the PUN

$$Y = \overline{(A + B) * C} = \overline{(A + B)} + \bar{C} = (\bar{A} * \bar{B}) + \bar{C}$$

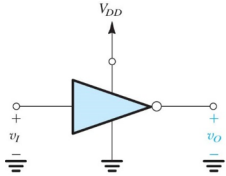
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Digital/Binary and Analog Linear/Small-Signal Abstraction

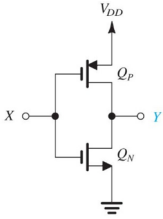
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Inverter Gate Delay (book 15.4)

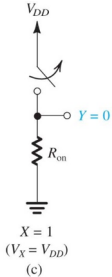
# CMOS Inverter Model



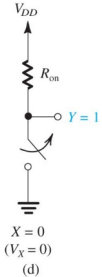
(a)



(b)

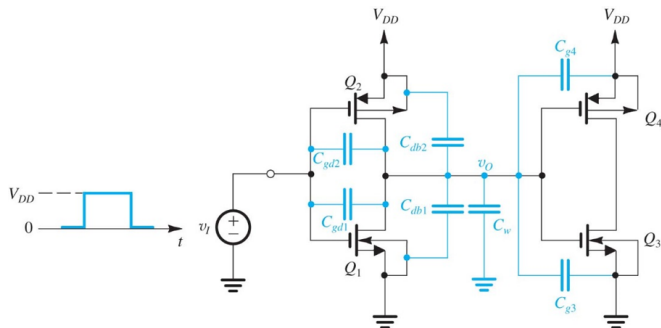


$X = 1$   
( $V_X = V_{DD}$ )  
(c)



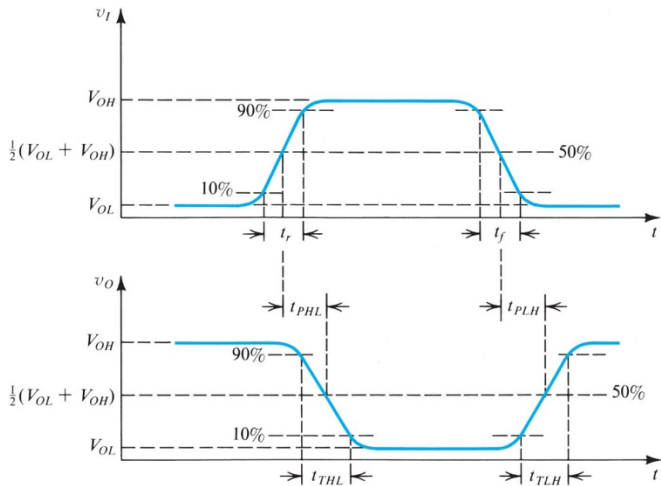
$X = 0$   
( $V_X = 0$ )  
(d)

# CMOS Inverter HF Model



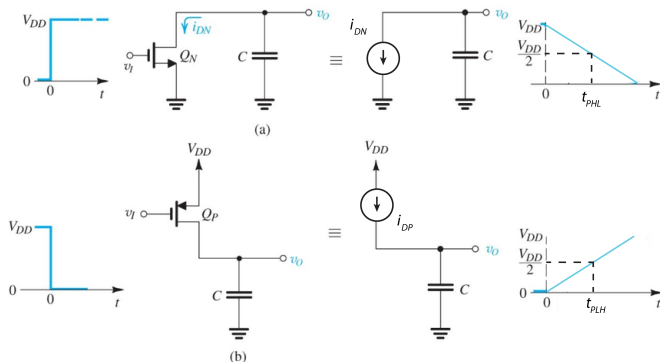
$$C = 2 * (C_{gd1} + C_{gd2}) + C_{db1} + C_{db2} + C_{g3} + C_{g4} + C_w \quad (15.59)$$

# Propagation delay and transition time





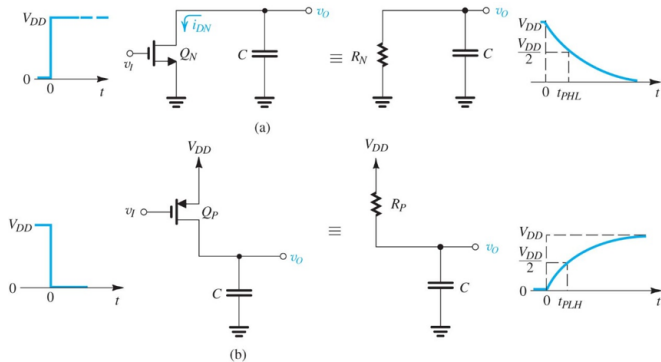
# IC model for delay



$$\hat{i}_{DN} = \frac{i_{DN}(V_{DD}) + i_{DN}(\frac{V_{DD}}{2})}{2} \quad (15.47)$$

$$t_{PHL(LH)} = \frac{CV_{DD}}{2\hat{i}_{DN(DP)}} = \frac{\alpha_{n(p)}C}{k_{n(p)}V_{DD}} \quad (15.46, 15.50)$$

# RC model for delay



$$R_{N(P)} = \frac{12.5(30)}{(W/L)_{n(p)}} \text{ k}\Omega \quad (15.56)$$

$$t_{PHL(LH)} = 0.69 R_{n(p)} C \quad (15.54)$$

# Observations

- ▶ To balance  $t_{PHL}$  and  $t_{PLH}$  often pFETs in digital circuits are chosen to be wider than nFETs
- ▶ In contrast to analog circuits, here maximizing speed ( $f_T$ ) is preferred before maximizing gain ( $A_0$ ), i.e. digital transistors are most often minimum length. However, small gain still has a negative impact on noise margin.
- ▶ These models are really crude and only give an idea of which parameters to tweak in which direction for an expected result. For reasonable absolute estimates one needs to consult transistor level simulation at least, or even post-layout simulation.